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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	09/362,192
				Filing Date	July 28, 1999
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2812
				Examiner Name	V. Simkovic
Sheet 1 of 1	Attorney Docket Number		740756-2011		

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
<i>AS</i>		5,956,581		YAMAZAKI et al.	09/21/1999	

FOREIGN PATENT DOCUMENTS							
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	<i>[Signature]</i>	Date Considered	5/11/02
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O-1449
8-83)U.S. Department of Commerce
Patent and Trademark Office

Atty Docket 0756-2011

Serial No. 09/362,192

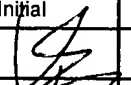
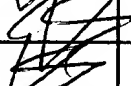
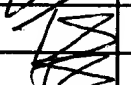
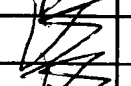
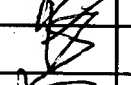
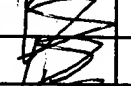
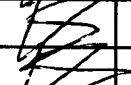
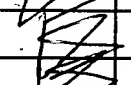
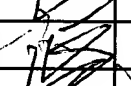
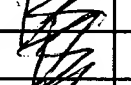


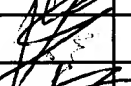
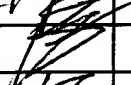
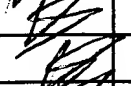
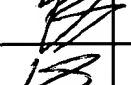

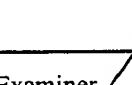
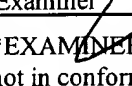
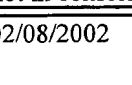

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 28, 1999

Group Art Unit: 2812

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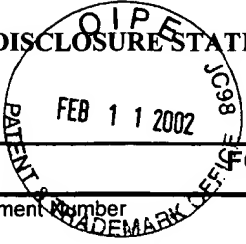

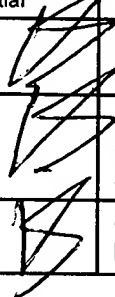
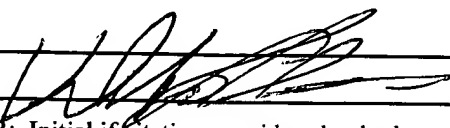
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Examiner

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TO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0756-2011		Serial No. 09/362,192	
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FOREIGN PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No	
	04-035021	02/05/1992	JP			Eng Abst	
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